MMBT589LT1G, NSVMMBT589LT1G

High Current Surface Mount PNP Silicon Switching Transistor for Load Management in Portable Applications

Features

- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS $(T_A = 25^{\circ}C)$

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V _{CEO}	-30	Vdc
Collector - Base Voltage	V _{CBO}	- 50	Vdc
Emitter-Base Voltage	V _{EBO}	-5.0	Vdc
Collector Current – Continuous	I _C	-1.0	Adc
Collector Current – Peak	I _{CM}	-2.0	Α

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board, (Note 1) T _A = 25°C Derate above 25°C	P _D	310 2.5	mW mW/°C
Thermal Resistance Junction-to-Ambient (Note 1)	$R_{\theta JA}$	403	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T _A = 25°C Derate above 25°C	P _D	710 5.7	mW mW/°C
Thermal Resistance Junction-to-Ambient (Note 2)	$R_{\theta JA}$	176	°C/W
Total Device Dissipation (Ref. Figure 8) (Single Pulse < 10 sec.)	P _{Dsingle}	575	mW
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. FR-4 @ Minimum Pad
- 2. FR-4 @ 1.0 X 1.0 inch Pad



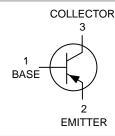
ON Semiconductor®

www.onsemi.com

30 VOLTS, 2.0 AMPS PNP TRANSISTORS



SOT-23 (TO-236) CASE 318 STYLE 6



MARKING DIAGRAM



G3 = Device Code

M = Date Code*

= Pb-Free Package

(Note: Microdot may be in either location)
*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBT589LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
NSVMMBT589LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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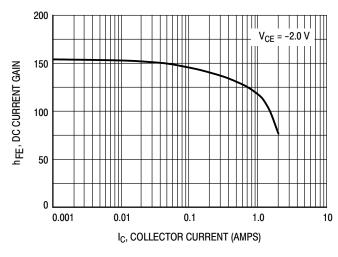
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector – Emitter Breakdown Voltage $(I_C = -10 \text{ mAdc}, I_B = 0)$	V _(BR) CEO	 -30	_	Vdc
Collector – Base Breakdown Voltage $(I_C = -0.1 \text{ mAdc}, I_E = 0)$	V _{(BR)CBO}	-50	-	Vdc
Emitter – Base Breakdown Voltage (I _E = -0.1 mAdc, I _C = 0)	V _{(BR)EBO}	-5.0	-	Vdc
Collector Cutoff Current (V _{CB} = -30 Vdc, I _E = 0)	Ісво	_	-0.1	μAdc
Collector–Emitter Cutoff Current (V _{CES} = -30 Vdc)	I _{CES}	_	-0.1	μAdc
Emitter Cutoff Current (V _{EB} = -4.0 Vdc)	I _{EBO}	_	-0.1	μAdc
ON CHARACTERISTICS				
DC Current Gain (Note 3) (Figure 1) $ \begin{aligned} &(I_C = -1.0 \text{ mA, } V_{CE} = -2.0 \text{ V}) \\ &(I_C = -500 \text{ mA, } V_{CE} = -2.0 \text{ V}) \\ &(I_C = -1.0 \text{ A, } V_{CE} = -2.0 \text{ V}) \\ &(I_C = 2.0 \text{ A, } V_{CE} = -2.0 \text{ V}) \end{aligned} $	h _{FE}	100 100 80 40	- 300 - -	-
Collector – Emitter Saturation Voltage (Note 3) (Figure 3) $ \begin{pmatrix} I_C = -0.5 \text{ A}, I_B = -0.05 \text{ A} \end{pmatrix} $ $ \begin{pmatrix} I_C = -1.0 \text{ A}, I_B = 0.1 \text{ A} \end{pmatrix} $ $ \begin{pmatrix} I_C = -2.0 \text{ A}, I_B = -0.2 \text{ A} \end{pmatrix} $	V _{CE(sat)}	- - -	-0.25 -0.30 -0.65	V
Base – Emitter Saturation Voltage (Note 3) (Figure 2) $(I_C = -1.0 \text{ A}, I_B = -0.1 \text{ A})$	V _{BE(sat)}	_	-1.2	V
Base – Emitter Turn–on Voltage (Note 3) (I _C = -1.0 A, V _{CE} = -2.0 V)	V _{BE(on)}	-	-1.1	V
Cutoff Frequency ($I_C = -100 \text{ mA}$, $V_{CE} = -5.0 \text{ V}$, $f = 100 \text{ MHz}$)	f⊤	100	_	MHz
Output Capacitance (f = 1.0 MHz)	Cobo	_	15	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle ≤ 2%

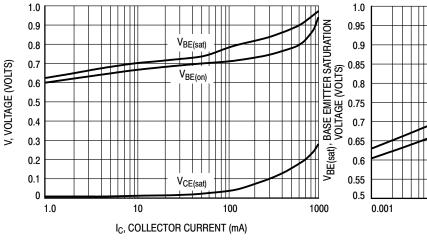
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230 V_{CE} = -1.0 V 210 125°C 190 hFE, DC CURRENT GAIN 170 150 25°C 130 110 90 -55°C 70 50 1.0 100 1000 IC, COLLECTOR CURRENT (mA)

Figure 1. DC Current Gain versus Collector Current

Figure 2. DC Current Gain versus Collector Current



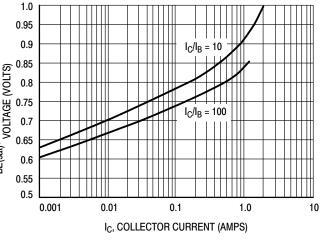
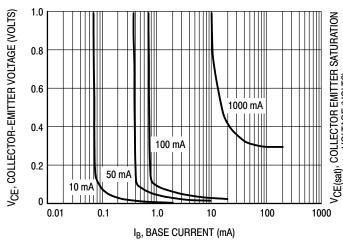


Figure 3. "On" Voltages

Figure 4. Base Emitter Saturation Voltage versus Collector Current



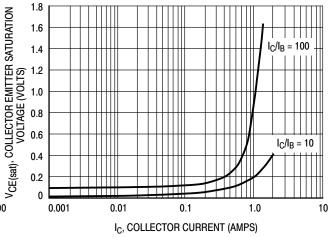


Figure 5. Collector Emitter Saturation Voltage versus Collector Current

Figure 6. Collector Emitter Saturation Voltage versus Collector Current

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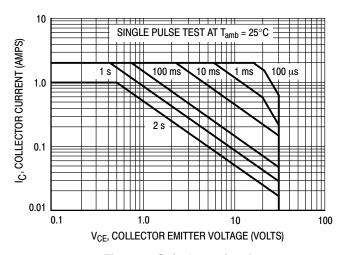


Figure 7. Safe Operating Area

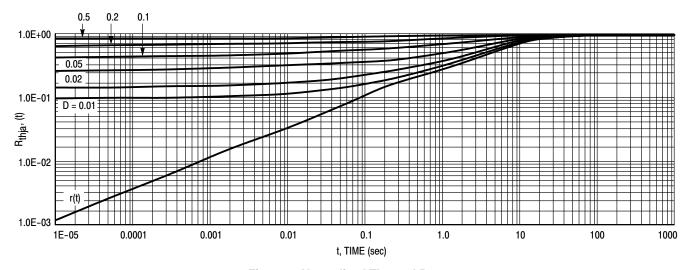


Figure 8. Normalized Thermal Response

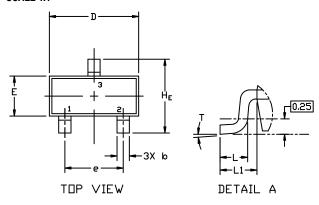


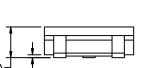


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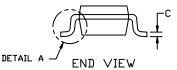
DATE 01 MAR 2023







SIDE VIEW



NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- CONTROLLING DIMENSION: MILLIMETERS
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS		INCHES			
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
Ε	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0*		10°	0*		10°

GENERIC MARKING DIAGRAM*

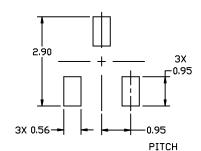


XXX = Specific Device Code

= Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

STYLES ON PAGE 2

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DATE 01 MAR 2023

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	ı	
STYLE 9:	STYLE 10:	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN		PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE		2. CATHODE	2. DRAIN	2. GATE
3. CATHODE	3. GATE		3. ANODE	3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	I PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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